Silicon NPN Power Transistors 2SC2761

DESCRIPTION

- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls



Fig.1 simplified outline (TO-3) and symbol

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		30	A
I_B	Base current		6	A
P_C	Collector power dissipation	T_C=25℃	200	W
T_j	Junction temperature		200	℃
T_{stg}	Storage temperature		-65~200	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=0.1A ; I_B=0	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1m A ; I_E=0	450			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1m A ; I_C=0	7			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=20A; I_B=4A			1.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=20A; I_B=4A			1.7	V
I_{CBO}	Collector cut-off current	V_{CB}=450V I_E=0			100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			100	μA
h_{FE}	DC current gain	I_C=15A ; V_{CE}=2V	8			

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PACKAGE OUTLINE

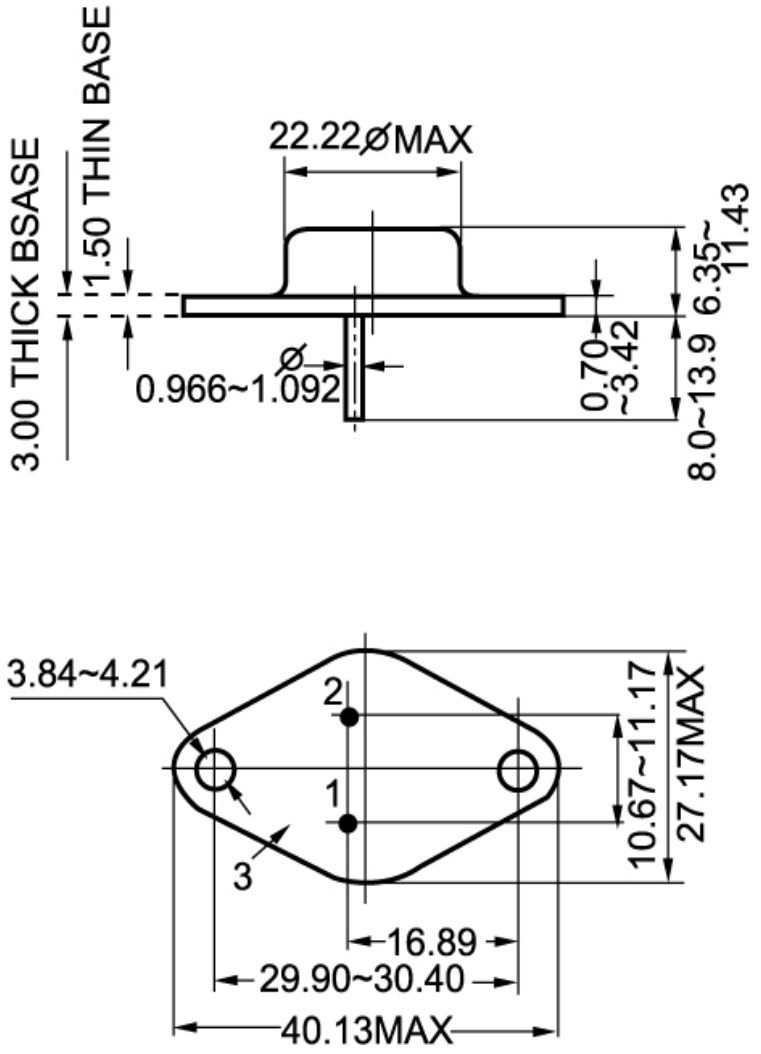


Fig.2 Outline dimensions